

BAS19 SWITCHING DIODE

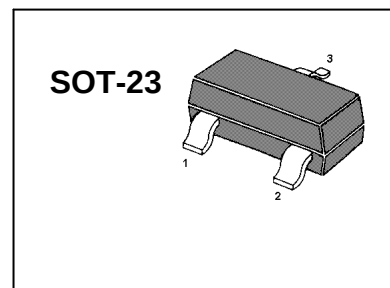
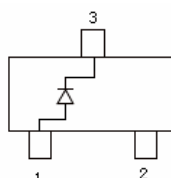
FEATURES

Fast Switching Speed

Surface Mount Package Ideally Suited for Automatic Insertion

For General Purpose Switching Applications

High Conductance



Marking: JP

Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V _{RM}	100	V
DC Blocking Voltage	V _R		
Average Rectified Output Current	I _O	200	mA
Power Dissipation	P _d	250	mW
Thermal Resistance. Junction to Ambient Air	R _{θJA}	500	°C/W
Junction temperature	T _J	150	°C
Storage temperature range	T _{STG}	-65-150	°C

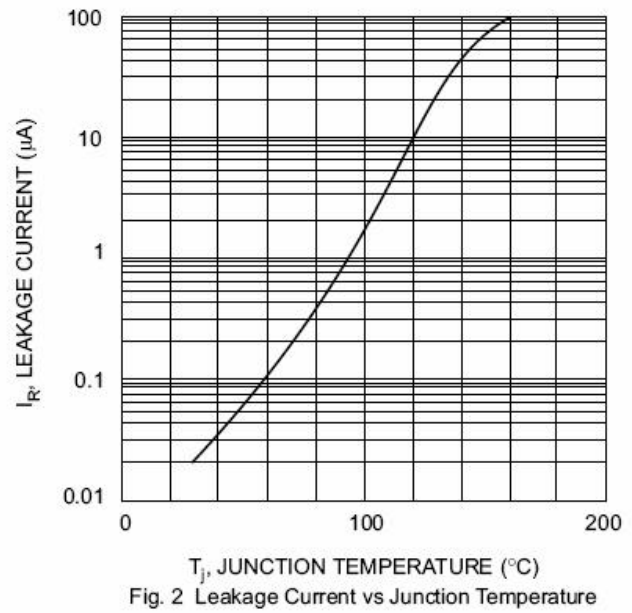
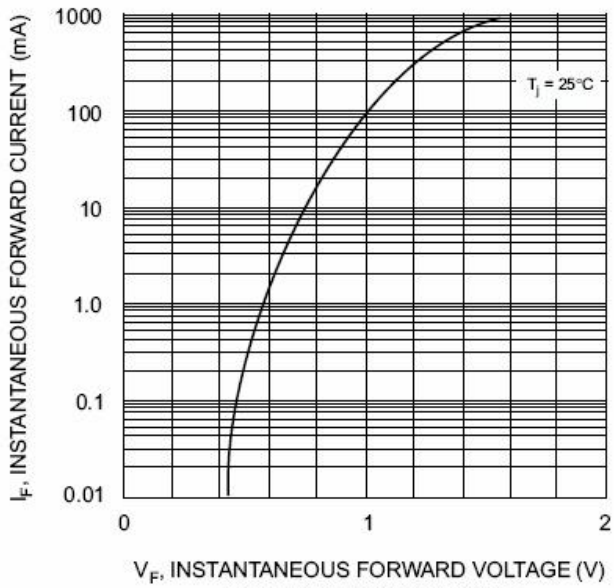
ELECTRICAL CHARACTERISTICS (T_{amb}=25°C

unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _{(BR)R}	I _R = 100μA	100		V
Reverse voltage leakage current	I _R	V _R =100V		0.1	μA
Forward voltage	V _F	I _F =100mA I _F =200mA		1 1.25	V
Junction Capacitance	C _J	V _R =0V, f=1MHz		5	pF
Reveres recovery time	t _{rr}	I _F =I _R =30mA, I _{rr} =0.1×I _R		50	nS

Typical Characteristics

BAS19



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23

